

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

Claims 1-11 (canceled)

12. An amplifier circuit, comprising:

a main stage amplifier connected between an RF input (HFin) and an RF output;

and

at least one secondary stage amplifier, which is connected in parallel to the main stage amplifier between the RF input and the RF output, wherein the secondary stage amplifier comprises:

an input bipolar transistor having at least one of a collector terminal and an emitter terminal high frequency-coupled to the RF input;

an output bipolar transistor having a base terminal high frequency-coupled to the base terminal of the input bipolar transistor, the output bipolar transistor having at least one of a collector terminal and an emitter terminal high frequency coupled to the RF output, wherein the output bipolar transistor is further operably coupled to a supply voltage terminal.

13. The amplifier circuit according to claim 12, wherein a DC decoupling device is interposed between the supply voltage terminal and the RF output.

14. The amplifier circuit according to claim 12, wherein the secondary stage amplifier further has a bias input, the bias input operable to apply a bias voltage to the base terminal of the input bipolar transistor and apply a bias voltage to the base terminal of the output bipolar transistor, to thereby activate the secondary stage amplifier.

15. The amplifier circuit according to claim 14, wherein the collector of the input bipolar transistor is high frequency- coupled to the RF input, and wherein the collector of the output bipolar transistor is high frequency-coupled to the RF output, wherein application of the bias voltage operates to bias the collector base diode of the input bipolar transistor in flow direction, and to provide the base terminal of the output bipolar transistor with an operating point potential when the secondary stage amplifier is switched-on.

16. The amplifier circuit according to claim 15, wherein the bias input is operable to apply of the bias voltage such that the collector base diode of the input bipolar transistor and the collector base diode of the output bipolar transistor are reverse-polarized when the secondary stage amplifier is switched-off.

17. The amplifier circuit according to claim 14, wherein the bias input is operable to apply the bias voltage such that the bias voltage switches the secondary stage amplifier on and off, depending on a level of the RF input signal.

18. The amplifier circuit according to claim 12, wherein the main stage amplifier has an amplifier bipolar transistor, whose base terminal is connected to the RF input, wherein the input bipolar transistor of the secondary stage amplifier is connected to draw the base potential of the amplifier bipolar transistor on such a potential that the main stage amplifier is switched-off when the secondary stage amplifier is switched-on.

19. The amplifier circuit according to claim 14, wherein the bias input includes a bias terminal and a resistor connected between the bias terminal and the base terminals of the input bipolar transistor and the output bipolar transistor.

20. The amplifier circuit according to claim 19, wherein a further resistor is connected between the base terminal of the at least one of the input bipolar transistor and the output bipolar transistor and the resistor.

21. The amplifier circuit according to claim 14, wherein the bias input comprises a first bias terminal and a second bias terminal, a first resistor connected between the first bias voltage terminal and the base terminal of the input bipolar transistor, and a second resistor connected between the second bias terminal and the base terminal of the output bipolar transistor, and wherein the base terminals of the input bipolar transistor and the output bipolar transistor are coupled via a capacitor.

22. The amplifier circuit according to claim 12, wherein a diode is connected between the terminal of the output bipolar transistor that is high frequency-coupled to the RF output and the RF output, wherein the diode is operated in flow direction when the secondary stage amplifier is switched-on.

23. The amplifier circuit according to claim 22, wherein a high-impedance resistor is connected in parallel to the diode.

24. An amplifier circuit; comprising:

a main stage amplifier connected between an RF input and an RF output, the main stage amplifier having an amplifier bipolar transistor, the amplifier bipolar transistor having a base terminal is connected to the RF input; and

at least one secondary stage circuit, which is connected in parallel to the main stage amplifier between the RF input and the RF output, wherein the secondary stage circuit comprises:

a first bipolar transistor having at least one of a collector terminal and an emitter terminal high frequency-coupled to the RF input;

a second bipolar transistor having a base terminal high frequency-coupled to the base terminal of the first bipolar transistor, the second bipolar transistor having at least one of a collector terminal and an emitter terminal high frequency coupled to the RF output, wherein the second bipolar transistor is further operably coupled to a supply voltage terminal, the supply voltage terminal DC-decoupled from the RF output,

wherein the first bipolar transistor of the secondary stage circuit is connected to draw the base potential of the amplifier bipolar transistor on such a potential that the main stage amplifier is switched-off when the secondary stage circuit is switched-on.

25. The amplifier circuit according to claim 24, further comprising at least one capacitor interposed between the supply voltage terminal and the RF output.

26. The amplifier circuit according to claim 24, wherein the secondary stage circuit further has a bias input, the bias input operable to apply a bias voltage to the base terminal of the first bipolar transistor and apply a bias voltage to the base terminal of the second bipolar transistor, to thereby activate the secondary stage circuit.

27. The amplifier circuit according to claim 26, wherein the collector of the first bipolar transistor is high frequency- coupled to the RF input, and wherein the collector of the second bipolar transistor is high frequency-coupled to the RF output, wherein application of the bias voltage operates to bias the collector base diode of the first bipolar transistor in flow direction, and to provide the base terminal of the second bipolar transistor with an operating point potential when the secondary stage circuit is switched-on.

28. The amplifier circuit according to claim 26, wherein the bias input is operable to apply of the bias voltage such that the collector base diode of the first bipolar transistor

and the collector base diode of the second bipolar transistor are reverse-polarized when the secondary stage circuit is switched-off.

29. The amplifier circuit according to claim 26, wherein the bias input includes a bias terminal and a resistor connected between the bias terminal and the base terminals of the first bipolar transistor and the second bipolar transistor.

30. The amplifier circuit according to claim 26, wherein the bias input comprises a first bias terminal and a second bias terminal, a first resistor connected between the first bias voltage terminal and the base terminal of the first bipolar transistor, and a second resistor connected between the second bias terminal and the base terminal of the second bipolar transistor, and wherein the base terminals of the first bipolar transistor and the second bipolar transistor are DC-decoupled.

31. The amplifier circuit according to claim 24, wherein a diode is connected between the terminal of the second bipolar transistor that is high frequency-coupled to the RF output and the RF output, wherein the diode is operated in flow direction when the secondary stage circuit is switched-on.